

OPA6430UR

Ultra Bright

Ultra Red LED Chip

AlGaInP /GaAs

1. Material Substrate GaAs (N Type)
 Epitaxial Layer AlGaInP (P/N Type)

2. Electrode N (Cathode) Side Gold Alloy
 P (Anode) Side Gold Alloy

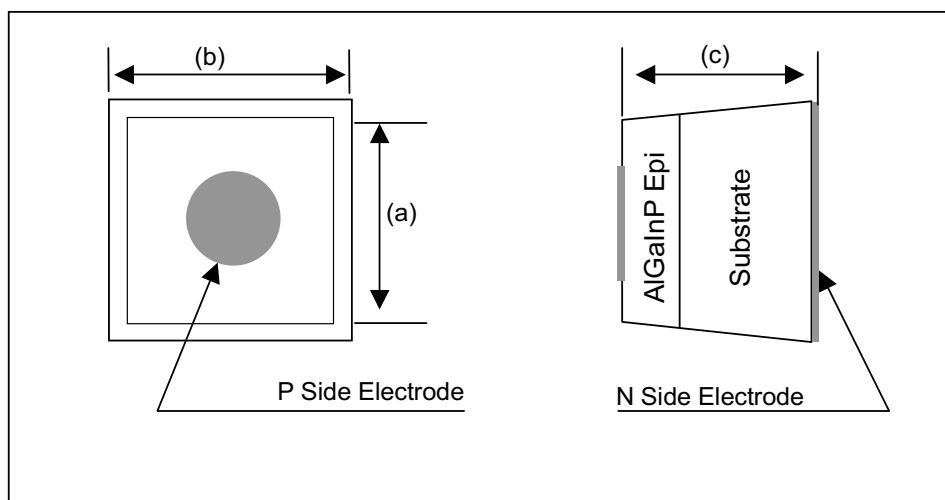
3. Electro-Optical Characteristics

Parameter	Symbol	Min	Typ	Max	Unit	Condition
Forward Voltage	$V_{F(1)}$		1.7		V	$I_F=1mA$
	$V_{F(2)}$		2.0	2.3	V	$I_F=20mA$
Reverse Voltage	V_R	6.0			V	$I_R=100\mu A$
Brightness	I_V	A	14	20	mcd	$I_F=20mA$
		B	18	30		
		C	25	40		
		D	30	50		
		E	40	60		
		F	50	70		
Wavelength	λ_P		639		nm	$I_F=20mA$
	λ_D		631		nm	$I_F=20mA$
	$\Delta\lambda$		20		nm	$I_F=20mA$

※ Note : Assembled into TO-18 Header without resin coating.

4. Mechanical Data

- (a) Emission Area ----- 11mil × 11mil
- (b) Bottom Area ----- 12mil × 12mil
- (c) Chip Thickness ----- 7mil



Knowledge*on Inc.

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